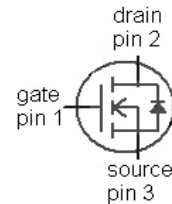


OptiMOS®3 Power-Transistor
Features

- Fast switching MOSFET for SMPS
- Optimized technology for DC/DC converters
- Qualified according to JEDEC¹⁾ for target applications
- N-channel, logic level
- Excellent gate charge x $R_{DS(on)}$ product (FOM)
- Very low on-resistance $R_{DS(on)}$
- Avalanche rated
- Pb-free plating; RoHS compliant

Product Summary

V_{DS}	30	V
$R_{DS(on),max}$	3.9	m Ω
I_D	50	A



Type	IPF039N03L G	IPU039N03L G
Package	PG-TO252-3-23	PG-TO251-3-21
Marking	039N03L	039N03L

Maximum ratings, at $T_j=25\text{ }^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Continuous drain current	I_D	$V_{GS}=10\text{ V}, T_C=25\text{ }^\circ\text{C}$	50	A
		$V_{GS}=10\text{ V}, T_C=100\text{ }^\circ\text{C}$	50	
		$V_{GS}=4.5\text{ V}, T_C=25\text{ }^\circ\text{C}$	50	
		$V_{GS}=4.5\text{ V}, T_C=100\text{ }^\circ\text{C}$	50	
Pulsed drain current ²⁾	$I_{D,pulse}$	$T_C=25\text{ }^\circ\text{C}$	350	
Avalanche current, single pulse ³⁾	I_{AS}	$T_C=25\text{ }^\circ\text{C}$	50	
Avalanche energy, single pulse	E_{AS}	$I_D=50\text{ A}, R_{GS}=25\text{ }\Omega$	115	mJ
Reverse diode dv/dt	dv/dt	$I_D=50\text{ A}, V_{DS}=24\text{ V}, di/dt=200\text{ A}/\mu\text{s}, T_{j,max}=175\text{ }^\circ\text{C}$	6	kV/ μs
Gate source voltage	V_{GS}		± 20	V

¹⁾ J-STD20 and JESD22

Maximum ratings, at $T_j=25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Power dissipation	P_{tot}	$T_C=25\text{ °C}$	94	W
Operating and storage temperature	T_j, T_{stg}		-55 ... 175	°C
IEC climatic category; DIN IEC 68-1			55/175/56	

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Thermal characteristics

Thermal resistance, junction - case	R_{thJC}		-	-	1.6	K/W
SMD version, device on PCB	R_{thJA}	minimal footprint	-	-	75	
		6 cm ² cooling area ⁴⁾	-	-	50	

Electrical characteristics, at $T_j=25\text{ °C}$, unless otherwise specified

Static characteristics

Drain-source breakdown voltage	$V_{(\text{BR})\text{DSS}}$	$V_{\text{GS}}=0\text{ V}, I_{\text{D}}=1\text{ mA}$	30	-	-	V
Gate threshold voltage	$V_{\text{GS(th)}}$	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=250\text{ }\mu\text{A}$	1	-	2.2	
Zero gate voltage drain current	I_{DSS}	$V_{\text{DS}}=30\text{ V}, V_{\text{GS}}=0\text{ V}, T_j=25\text{ °C}$	-	0.1	1	μA
		$V_{\text{DS}}=30\text{ V}, V_{\text{GS}}=0\text{ V}, T_j=125\text{ °C}$	-	10	100	
Gate-source leakage current	I_{GSS}	$V_{\text{GS}}=20\text{ V}, V_{\text{DS}}=0\text{ V}$	-	10	100	nA
Drain-source on-state resistance ⁵⁾	$R_{\text{DS(on)}}$	$V_{\text{GS}}=4.5\text{ V}, I_{\text{D}}=30\text{ A}$	-	4.2	5.2	$\text{m}\Omega$
		$V_{\text{GS}}=10\text{ V}, I_{\text{D}}=30\text{ A}$	-	3.3	3.9	
Gate resistance	R_{G}		-	1.6	-	Ω
Transconductance	g_{fs}	$ V_{\text{DS}} >2 I_{\text{D}} R_{\text{DS(on)max}}, I_{\text{D}}=30\text{ A}$	48	96	-	S

²⁾ See figure 3 for more detailed information

³⁾ See figure 13 for more detailed information

⁴⁾ Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70 μm thick) copper area for drain connection. PCB is vertical in still air.

⁵⁾ Measured from drain tab to source pin

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Dynamic characteristics

Input capacitance	C_{iss}	$V_{GS}=0\text{ V}, V_{DS}=15\text{ V},$ $f=1\text{ MHz}$	-	4000	5300	pF
Output capacitance	C_{oss}		-	1400	1900	
Reverse transfer capacitance	C_{rss}		-	81	120	
Turn-on delay time	$t_{d(on)}$	$V_{DD}=15\text{ V}, V_{GS}=10\text{ V},$ $I_D=30\text{ A}, R_G=1.6\ \Omega$	-	9	-	ns
Rise time	t_r		-	7	-	
Turn-off delay time	$t_{d(off)}$		-	35	-	
Fall time	t_f		-	5	-	

Gate Charge Characteristics⁶⁾

Gate to source charge	Q_{gs}	$V_{DD}=15\text{ V}, I_D=30\text{ A},$ $V_{GS}=0\text{ to }4.5\text{ V}$	-	12	-	nC
Gate charge at threshold	$Q_{g(th)}$		-	6.3	-	
Gate to drain charge	Q_{gd}		-	5.6	-	
Switching charge	Q_{sw}		-	11	-	
Gate charge total	Q_g		-	25	-	
Gate plateau voltage	$V_{plateau}$		-	2.9	-	V
Gate charge total	Q_g	$V_{DD}=15\text{ V}, I_D=30\text{ A},$ $V_{GS}=0\text{ to }10\text{ V}$	-	51	-	nC
Gate charge total, sync. FET	$Q_{g(sync)}$	$V_{DS}=0.1\text{ V},$ $V_{GS}=0\text{ to }4.5\text{ V}$	-	22	-	
Output charge	Q_{oss}	$V_{DD}=15\text{ V}, V_{GS}=0\text{ V}$	-	37	-	

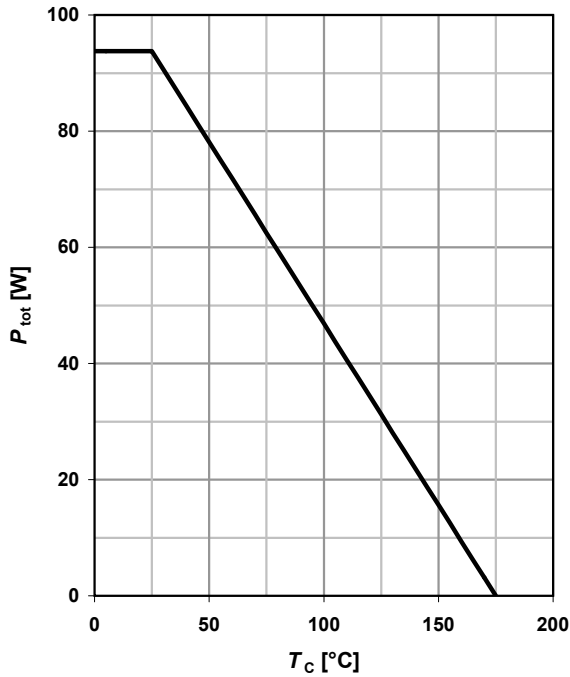
Reverse Diode

Diode continuous forward current	I_S	$T_C=25\text{ }^\circ\text{C}$	-	-	50	A
Diode pulse current	$I_{S,pulse}$		-	-	350	
Diode forward voltage	V_{SD}	$V_{GS}=0\text{ V}, I_F=30\text{ A},$ $T_j=25\text{ }^\circ\text{C}$	-	0.85	1.1	V
Reverse recovery charge	Q_{rr}	$V_R=15\text{ V}, I_F=I_S,$ $di_F/dt=400\text{ A}/\mu\text{s}$	-	-	20	nC

⁶⁾ See figure 16 for gate charge parameter definition

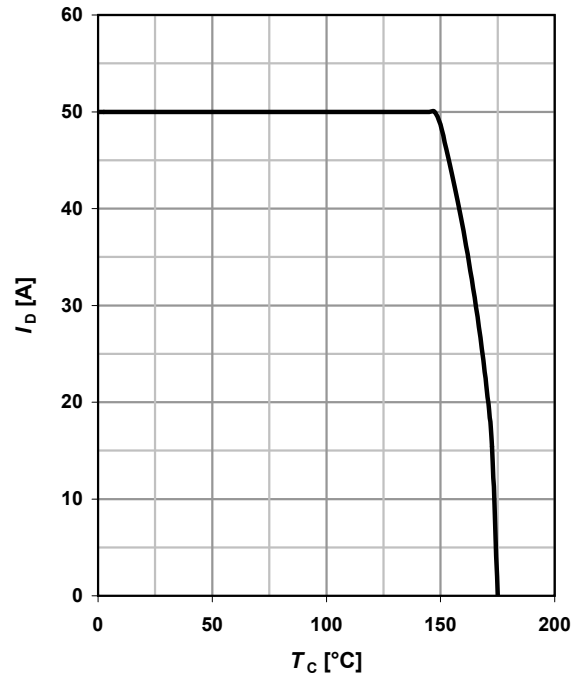
1 Power dissipation

$$P_{tot} = f(T_C)$$



2 Drain current

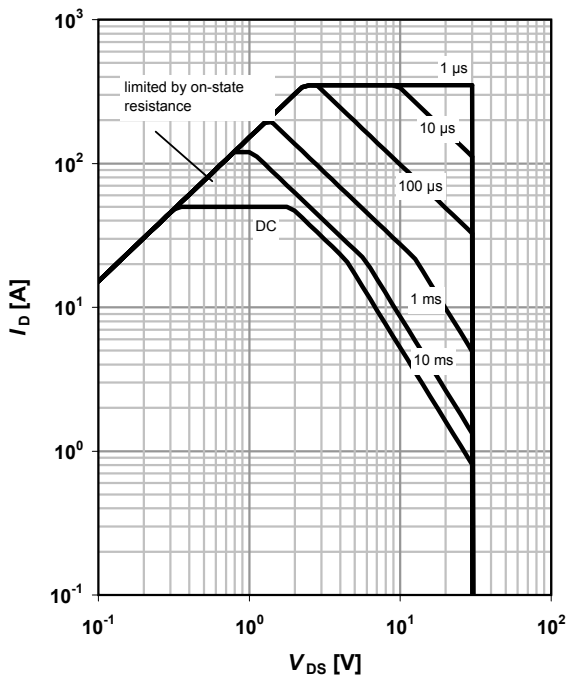
$$I_D = f(T_C); V_{GS} \geq 10 \text{ V}$$



3 Safe operating area

$$I_D = f(V_{DS}); T_C = 25 \text{ °C}; D = 0$$

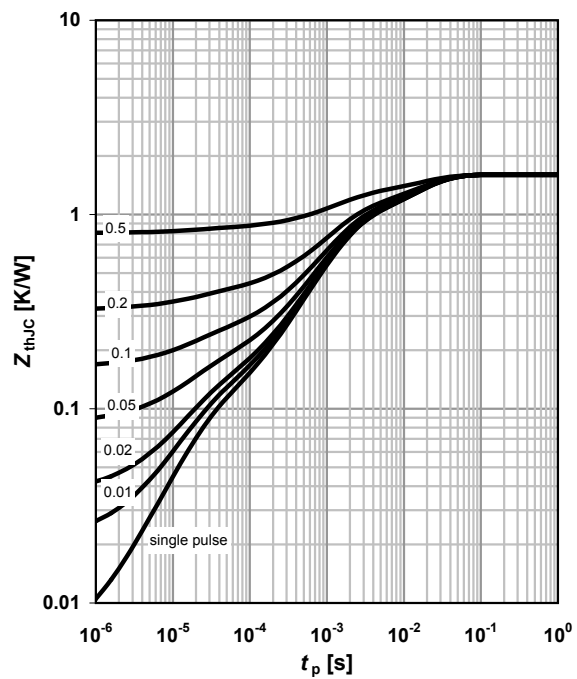
parameter: t_p



4 Max. transient thermal impedance

$$Z_{thJC} = f(t_p)$$

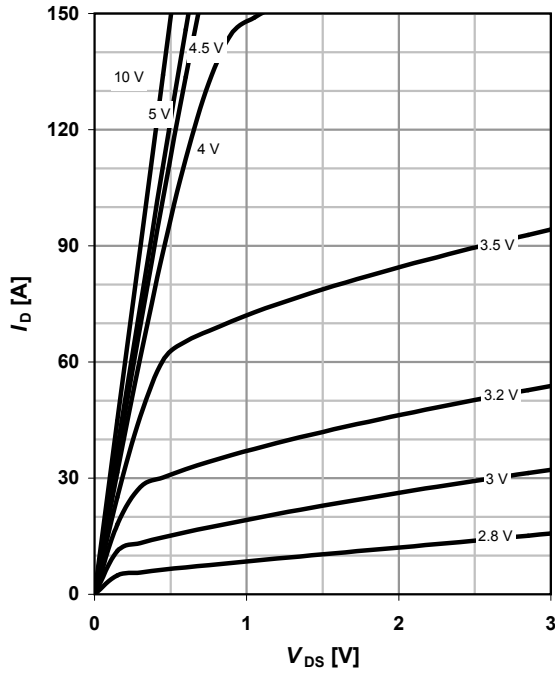
parameter: $D = t_p / T$



5 Typ. output characteristics

$I_D = f(V_{DS}); T_j = 25\text{ }^\circ\text{C}$

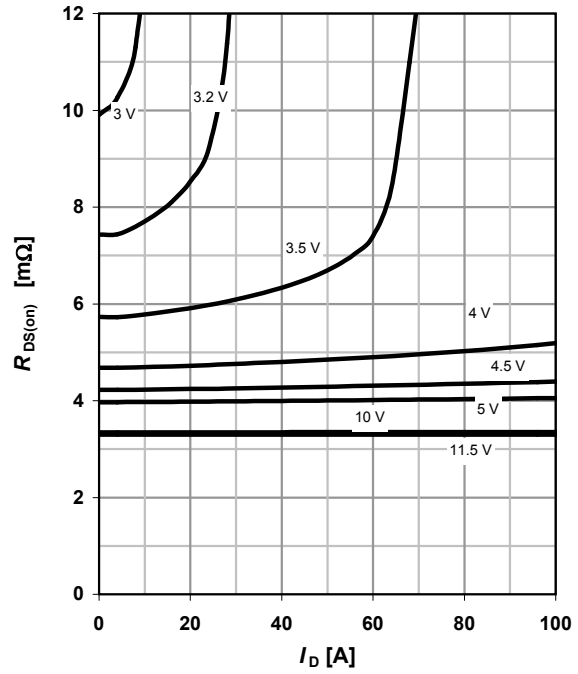
parameter: V_{GS}



6 Typ. drain-source on resistance

$R_{DS(on)} = f(I_D); T_j = 25\text{ }^\circ\text{C}$

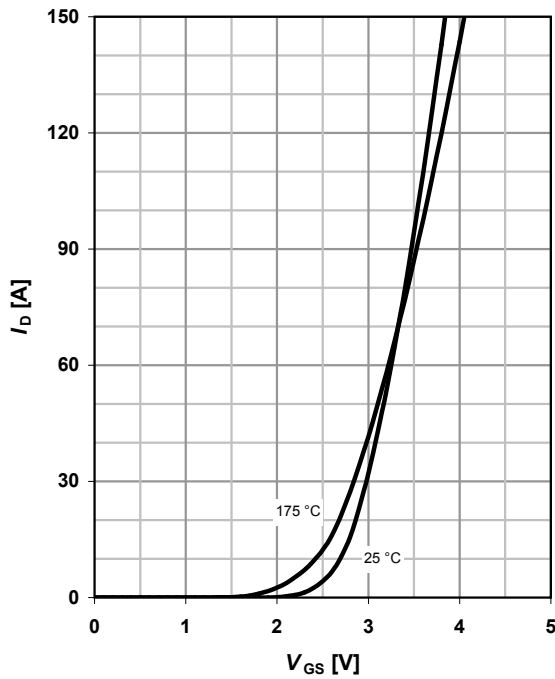
parameter: V_{GS}



7 Typ. transfer characteristics

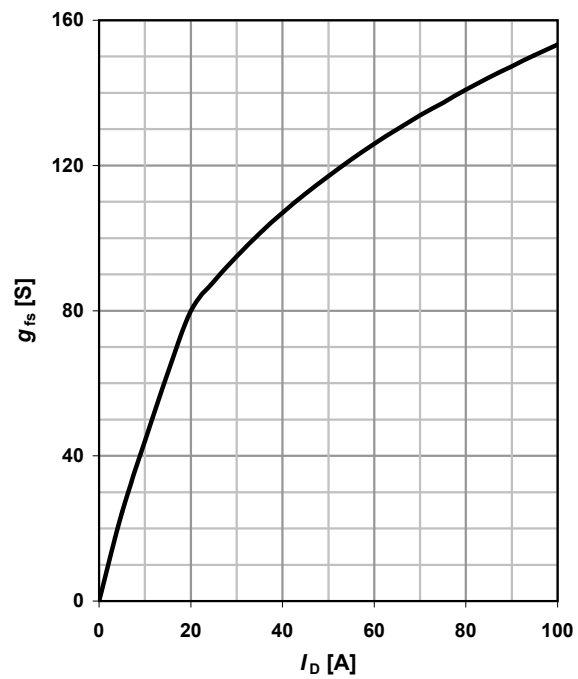
$I_D = f(V_{GS}); |V_{DS}| > 2|I_D|R_{DS(on)max}$

parameter: T_j



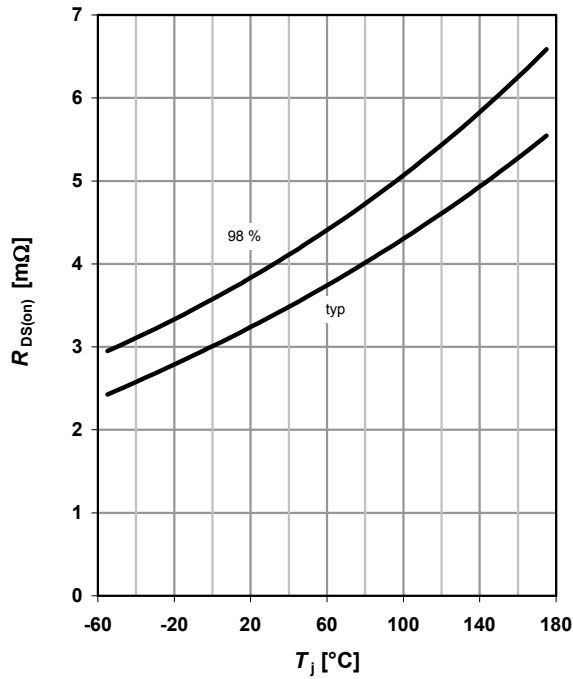
8 Typ. forward transconductance

$g_{fs} = f(I_D); T_j = 25\text{ }^\circ\text{C}$



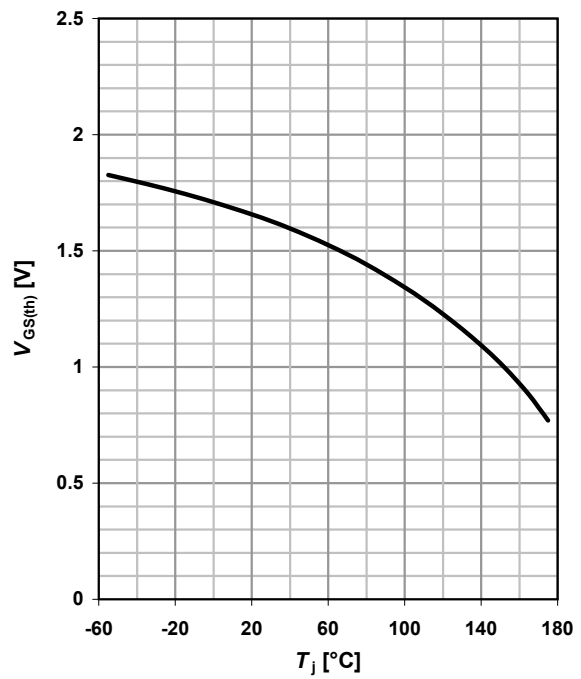
9 Drain-source on-state resistance

$R_{DS(on)} = f(T_j); I_D = 30 \text{ A}; V_{GS} = 10 \text{ V}$



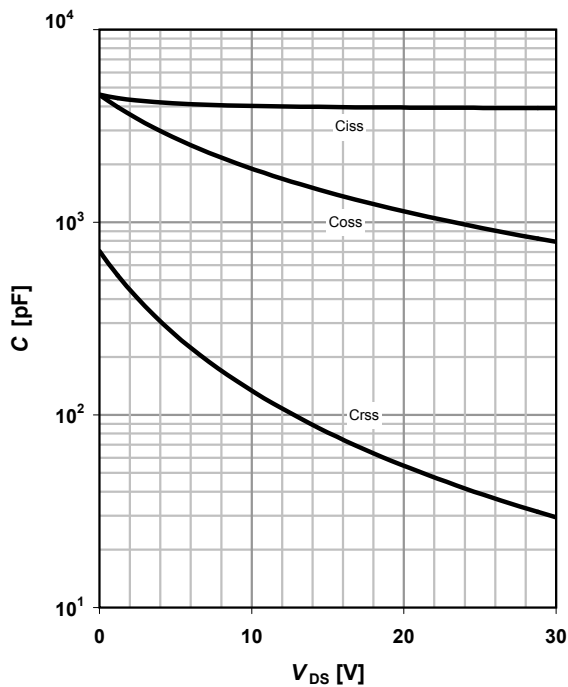
10 Typ. gate threshold voltage

$V_{GS(th)} = f(T_j); V_{GS} = V_{DS}; I_D = 250 \mu\text{A}$



11 Typ. capacitances

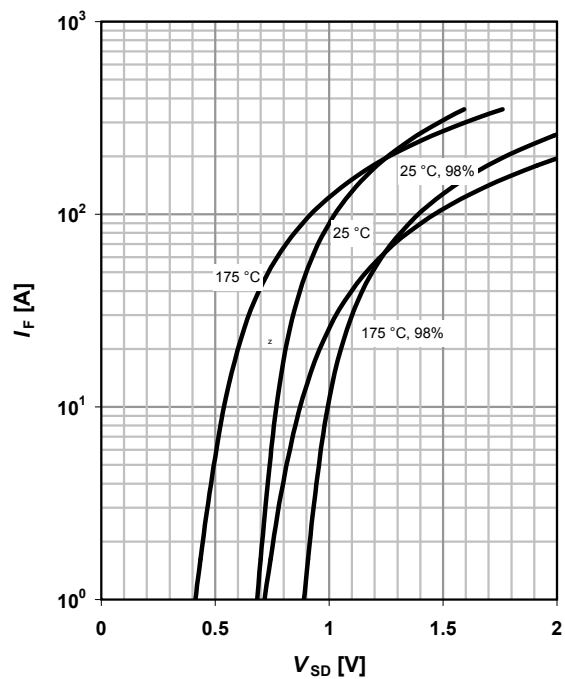
$C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$



12 Forward characteristics of reverse diode

$I_F = f(V_{SD})$

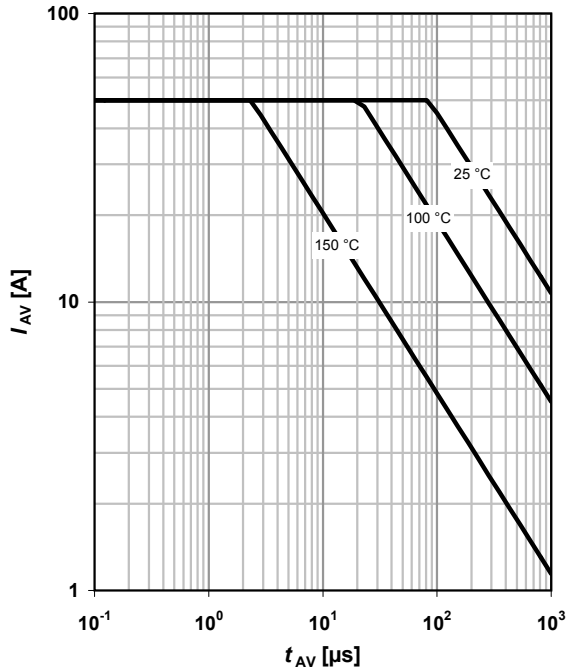
parameter: T_j



13 Avalanche characteristics

$I_{AS}=f(t_{AV}); R_{GS}=25 \Omega$

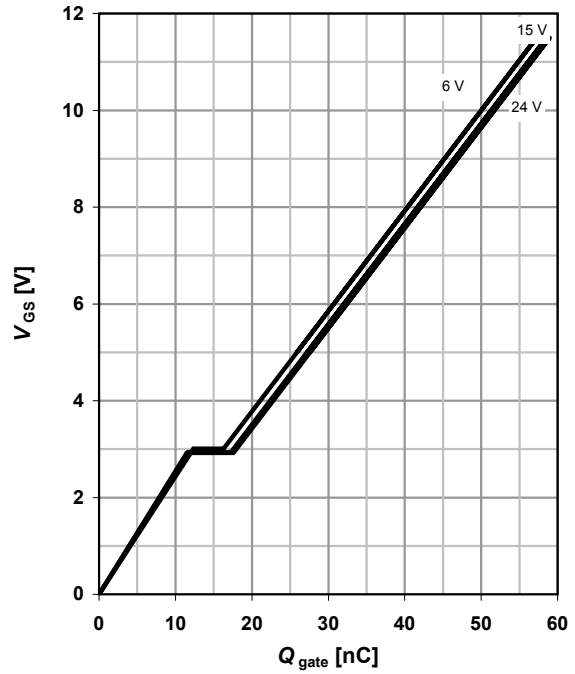
parameter: $T_{j(start)}$



14 Typ. gate charge

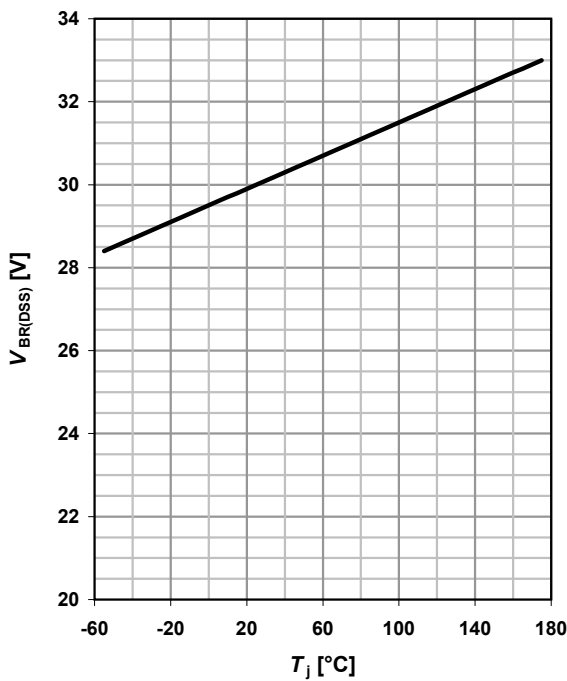
$V_{GS}=f(Q_{gate}); I_D=30 \text{ A pulsed}$

parameter: V_{DD}



15 Drain-source breakdown voltage

$V_{BR(DSS)}=f(T_j); I_D=1 \text{ mA}$

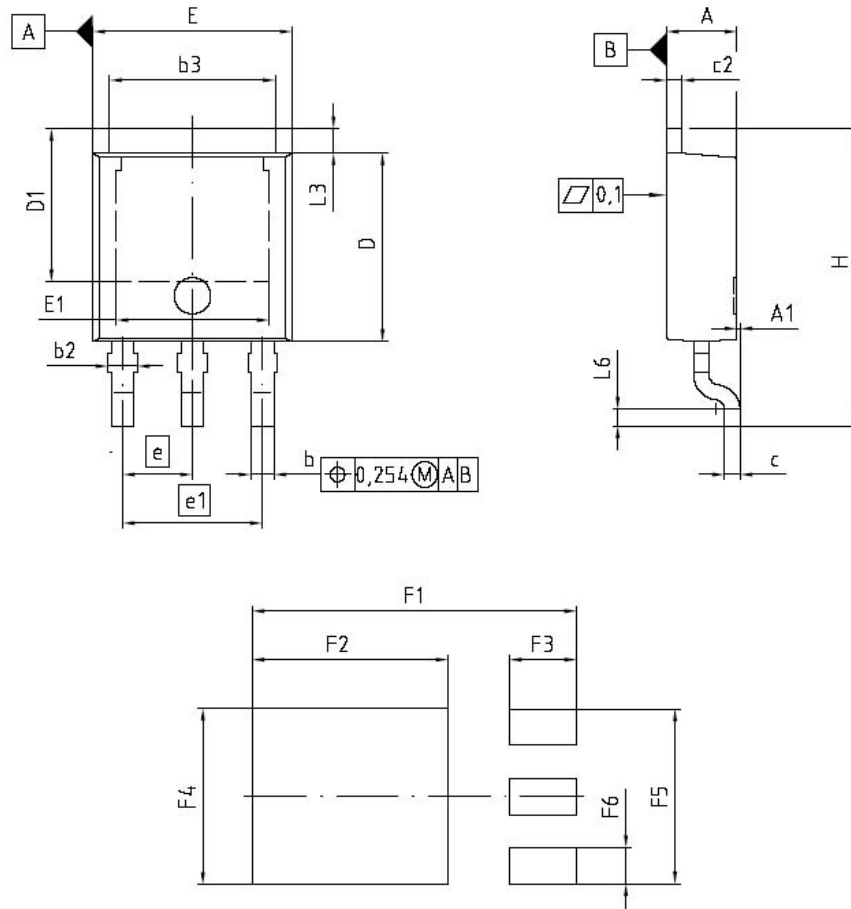


16 Gate charge waveforms



Package Outline

PG-TO252-3-23



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.159	2.413	0.085	0.095
A1	0.000	0.150	0.000	0.006
b	0.635	0.889	0.025	0.035
b2	0.650	1.150	0.026	0.045
b3	5.004	5.500	0.197	0.217
c	0.457	0.580	0.018	0.023
c2	0.460	0.980	0.018	0.039
D	5.969	6.223	0.235	0.245
D1	5.020	5.842	0.198	0.230
E	6.400	6.731	0.252	0.265
E1	4.850	5.207	0.191	0.205
e	2.286		0.090	
e1	4.572		0.180	
N	3		3	
H	9.400	10.480	0.370	0.413
L3	0.900	1.143	0.035	0.045
L4	0.584	0.950	0.023	0.037
L6	0.510	0.686	0.020	0.027
F1	10.500	10.700	0.413	0.421
F2	6.300	6.500	0.248	0.256
F3	2.100	2.300	0.083	0.091
F4	5.700	5.900	0.224	0.232
F5	5.660	5.860	0.222	0.231
F6	1.100	1.300	0.043	0.051

REFERENCE
-/-

SCALE
0 2.0 4mm

EUROPEAN PROJECTION

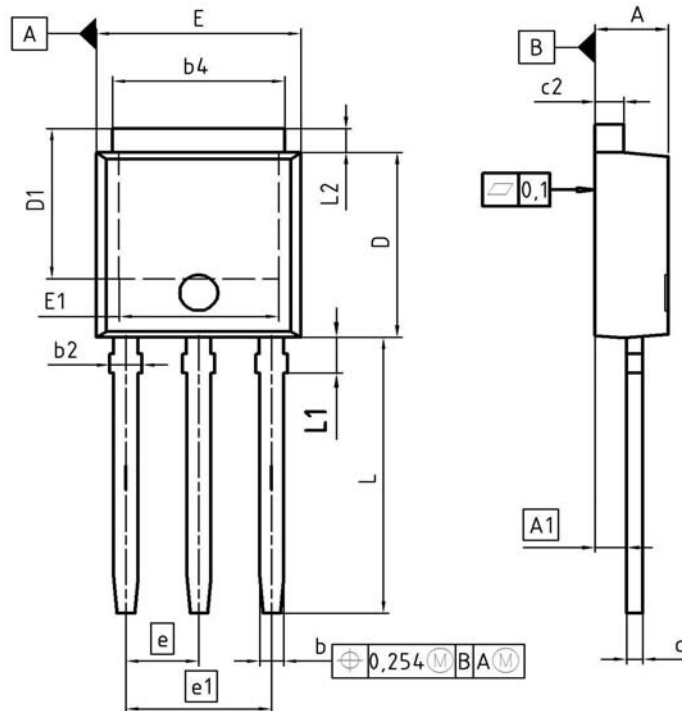
ISSUE DATE
21-09-2005

FILE
TO252_2

Package Outline

PG-TO251-3-21

PG-TO251-3-11: Outline



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.16	2.41	0.085	0.095
A1	0.90	1.14	0.035	0.045
b	0.64	0.89	0.025	0.035
b2	0.65	1.15	0.026	0.045
b4	4.95	5.50	0.195	0.217
c	0.46	0.60	0.018	0.024
c2	0.46	0.89	0.018	0.035
D	5.97	6.22	0.235	0.245
D1	5.04	5.77	0.198	0.227
E	6.35	6.73	0.250	0.265
E1	4.70	5.21	0.185	0.205
e	2.29		0.090	
e1	4.57		0.180	
N	3		3	
L	8.89	9.65	0.350	0.380
L1	1.90	2.29	0.075	0.090
L2	0.89	1.37	0.035	0.054

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03

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